

Temperature dependence of commercial 4H-SiC UV Schottky photodiodes for X-ray detection and spectroscopy

Article (Updated Version)

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Corrigendum

Corrigendum to ‘Temperature dependence of commercial 4H-SiC UV Schottky photodiodes for X-ray detection and spectroscopy’ [Nucl. Instrum. Methods Phys. Res. A 859 (2017) 76–82]



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The authors have been informed by the manufacturer of the photodiodes (SGLux SolGel Technologies GmbH, Berlin, Germany) that the photodiodes reported had Ohmic contacts rather than Schottky contacts.

The authors apologize for any inconvenience caused.

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